



N-channel MOSFET

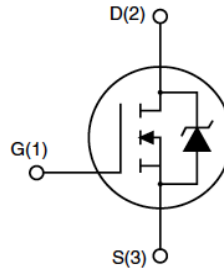
Features

- 100V,2.2A
- $R_{DS(ON)} = 250m\Omega$ (Typ.) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 260m\Omega$ (Typ.) @ $V_{GS} = 4.5V$
- High Density Cell Design for Ultra Low $R_{DS(ON)}$
- Fully Characterized Avalanche Voltage and Current
- Excellent Package for Good Heat Dissipation

Application

- Uninterruptible Power Supply(UPS)
- Hard Switched and High Frequency Circuits
- Power Switching application

Package



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
0102	TNM02K100KX	SOT-23	Ø180mm	8mm	3000 units

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units	
V _{DSS}	Drain-Source Voltage	100	V	
V _{GSS}	Gate-Source Voltage	±20	V	
I _D	Continuous Drain Current	T _C = 25°C	2.2	A
		T _C = 100°C	1.5	A
I _{DM}	Pulsed Drain Current ^{note1}	12	A	
P _D	Power Dissipation	T _A = 25°C	2.5 3.9 5	W
R _{θJA}	Thermal Resistance, Junction to Ambient	50	32 25	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C



Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} = 0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	1.0	1.8	3.0	V
R _{DSON}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} =10V, I _D =2A	-	250	280	mΩ
		V _{GS} =4.5V, I _D =1A	-	260	310	
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =3A	-	1.1	-	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} = 0V, f = 1.0MHz	-	330	-	pF
C _{oss}	Output Capacitance		-	88	-	pF
C _{rss}	Reverse Transfer Capacitance		-	15	-	pF
Q _g	Total Gate Charge	V _{DS} =50V, I _D =1A, V _{GS} =10V	-	5.2	-	nC
Q _{gs}	Gate-Source Charge		-	1.0	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	1.4	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =50V, R _L =39Ω, R _G =1Ω, V _{GS} =10V	-	14	-	ns
t _r	Turn-on Rise Time		-	54	-	ns
t _{d(off)}	Turn-off Delay Time		-	18	-	ns
t _f	Turn-off Fall Time		-	11	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	3	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =1A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



Typical Performance Characteristics

Figure 1: Output Characteristics

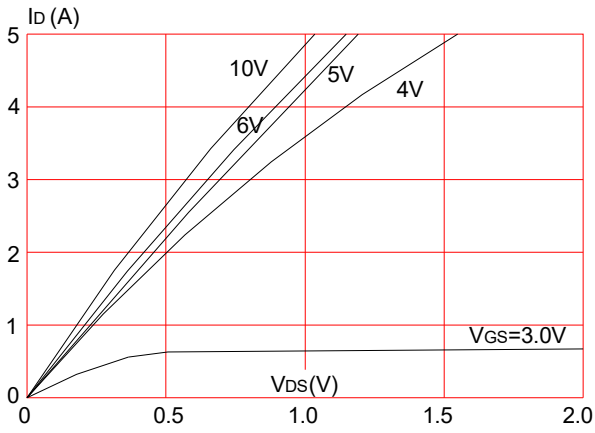


Figure 2: Typical Transfer Characteristics

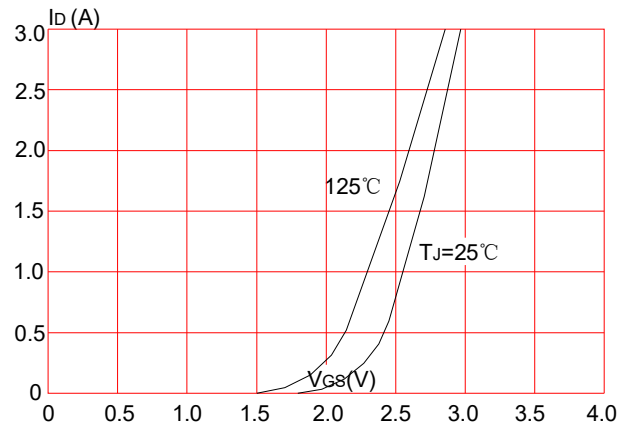


Figure 3: On-resistance vs. Drain Current

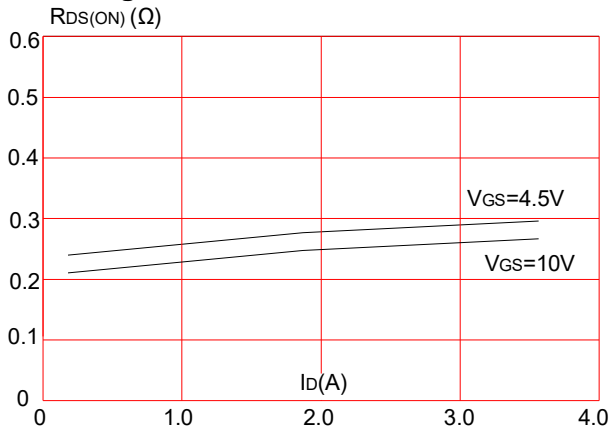


Figure 4: Body Diode Characteristics

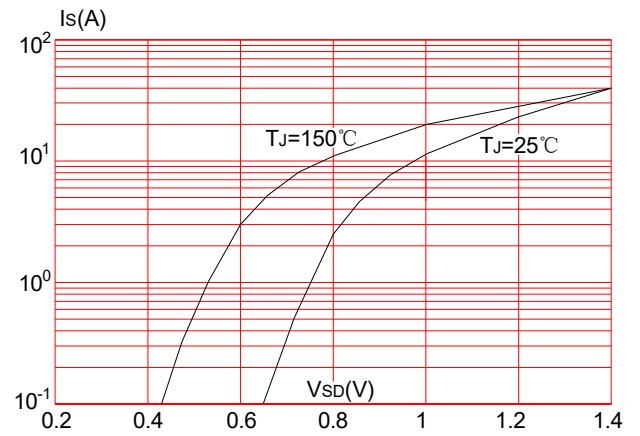


Figure 5: Gate Charge Characteristics

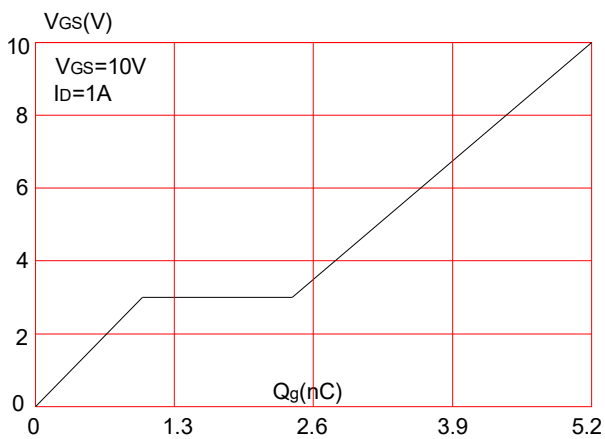


Figure 6: Capacitance Characteristics

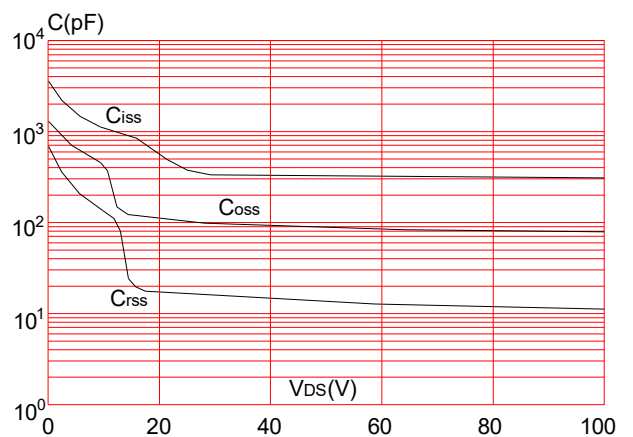


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

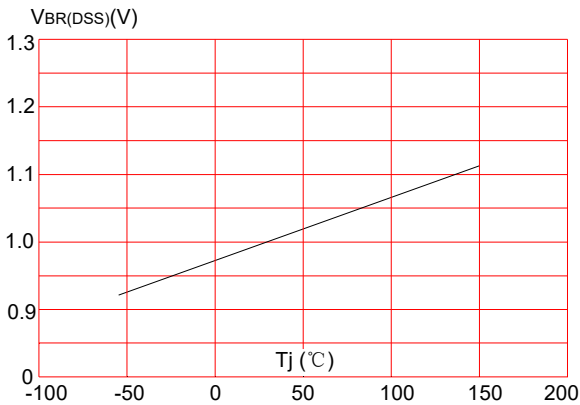


Figure 8: Normalized on Resistance vs. Junction Temperature

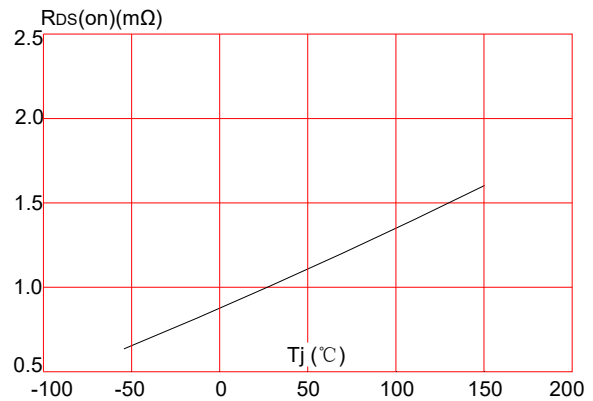


Figure 9: Maximum Safe Operating Area

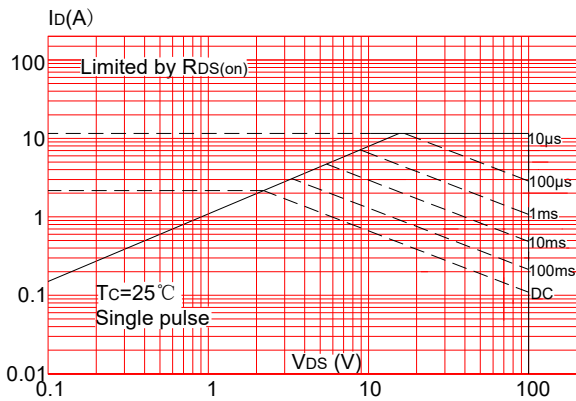


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

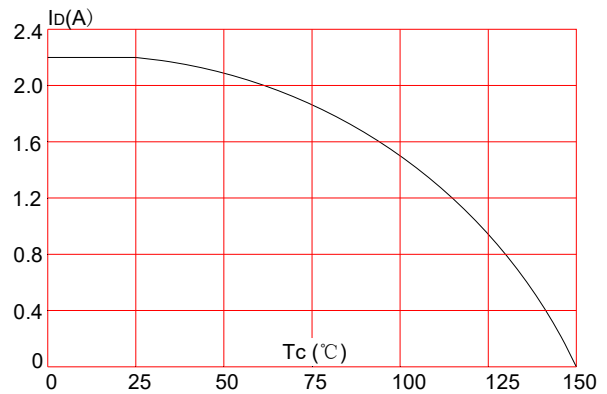
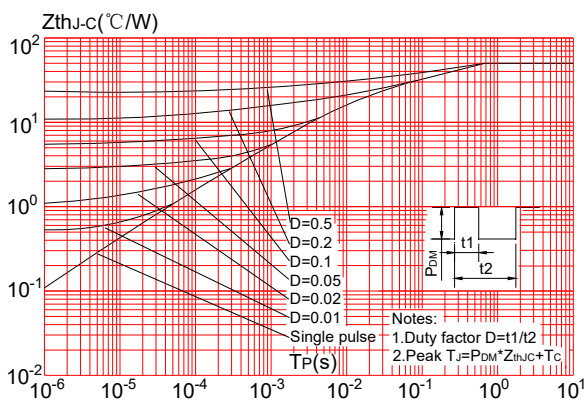
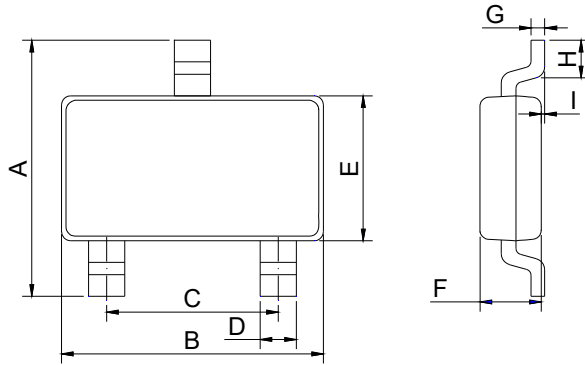
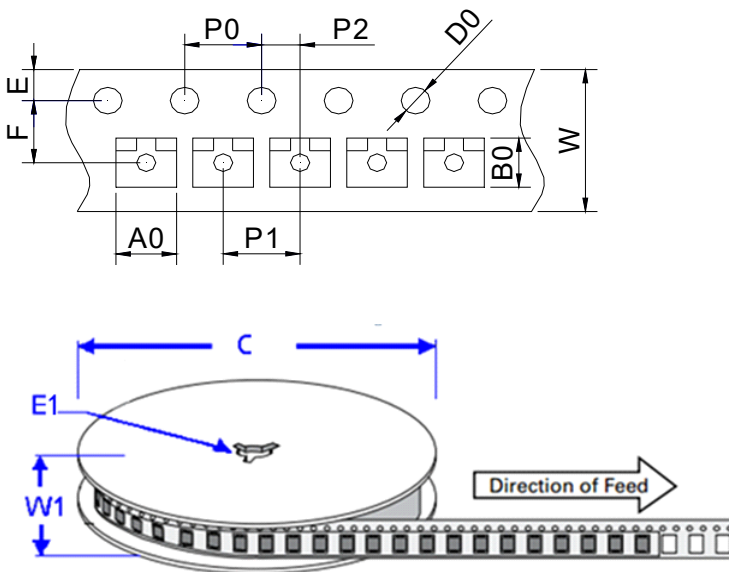


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data

SOT-23

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004

Package Information -SOT-23


Ref.	Dimensions	
	Millimeters	Inches
A0	3.15 ± 0.3	0.124 ± 0.012
B0	2.77 ± 0.3	0.109 ± 0.012
C	178	7.0
D0	1.50±0.1	0.059 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3±0.3	0.524± 0.012
F	3.5 ± 0.2	0.138 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	4.00 ± 0.2	0.157 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	8.00 ± 0.2	0.315 ± 0.008
W1	11.5±1.0	0.453 ± 0.039

Ordering Information-SOT-23

OUTLINE	PACKAGE TYPE	QUANTITY REEL	DESCRIPTION
TAPING	SOT-23	3,000pcs	7 inch reel pack

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